## 應用於 IEEE 802.11a/b/g 無線區域網路中 雙頻帶射頻接收器模組電路之設計與實現

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在這篇論文中設計並製作了兩大類的雙頻帶射頻接收器,第一類包含"切 換模式"和"並行模式",而第二類則是由"共存模式"和"寬頻模式"所組 成。設計部分完成了 2.4GHz 和 5GHz 頻帶的"切換模式"和"並行模式"前端接 受器以及 2.4/5GHz 雙頻帶"共存模式"前端接受器和"寬頻模式"低雜訊放大 器。而實作電路則包含一個 5.25GHz 頻帶的射頻前端接受器以及一個"共存式" 雙頻帶低雜訊放大器,並採用聯電 0.18 $\mu$ m 1P6M mixed-mode/RF CMOS 製程,智 森高頻元件模組和矽品 QFN 系列封裝。量測結果顯示當前端接收器消耗 30mA 電 流的同時,可以提供 18dB 的電壓增益(Av),1dB 增益壓縮點(P1dB)為-27dBm, 三階交調點(IIP3)和二階交調點(IIP2)分別為-3dBm 以及-12dBm,而雜訊指數 (NF)則為 6.4dB。低雜訊放大器有 27mW 功率消耗,可同時在 2.4GH 提供 6.7dB 的功率增益(S21),在 5.25GHz 則為-7.2dB,但由於輸入阻抗匹配的偏移,最大 增益點則發生在 2.74GHz,有 11.9dB 以及在 5.25GHz 為-5.1dB。

### The Design and Implementation of Dual Band RF Receiver

Module for IEEE 802.11a/b/g WLAN Applications

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### Abstract

In this thesis, two groups of dual band receiver are designed and fabricated. The first group consists of "switched mode" and "parallel mode". The other group is composed of "concurrent mode" and "wideband mode". The circuit design comprises 2.4 GHz and 5 GHz dual band receiver frontend for "switched mode" and "parallel mode", and 2.4/5 GHz dual band receiver frontend for "concurrent mode" as well as "wideband mode" LNA. The chip implementations include a 5.25 GHz receiver frontend and a concurrent dual band LNA employing UMC 0.18µm 1P6M mixed-mode/RF CMOS process, RF device models, and QFN series package provided by Giga-solution and SPIL respectively. The experimental results show that the receiver drains 30 mA of current and achieves the voltage gain of 18 dB, P1dB of -27 dBm, IIP3 of -12 dBm, IIP2 of -3 dBm, and NF of 6.4 dB. The LNA has a power gain of 6.7 dB at 2.4 GHz band, -7.2 dB at 5 GHz band having power dissipation of 18 mW, while the maximum power gain of this LNA is 11.9 dB at 2.74 GHz, -5.1 dB at 5.25 GHz due to the shift of input matching.

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